

Serial No. 09/817,120
Docket No. YOR920000231US1

AMENDMENTS TO THE SPECIFICATION:

Please revise the paragraph at lines 15-21 on page 7, as follows:

Thereafter, nitridation of W-Si occurs at about 750°C for about 30 min. with NH₃. Active NH₂, NH, species react with W-Si to form W-Si-N. This passivation layer has the structure of W-Si-N (e.g., see attached Auger Profile analysis results in Figure 5), and is effective in preventing W from being oxidized in the subsequent processing steps (e.g., see associated patent disclosure of "Method to Protect for Protecting Refractory Metal Thin Films Film Requiring High Temperature Processing in an Oxidizing Atmosphere and Structure Formed Thereby" (U.S. Patent application No. 09/337,550, having IBM Disclosure No. YOR8-1998-0774, currently U.S. Patent No. 6,238,737, issued May 29, 2001, incorporated herein by reference).